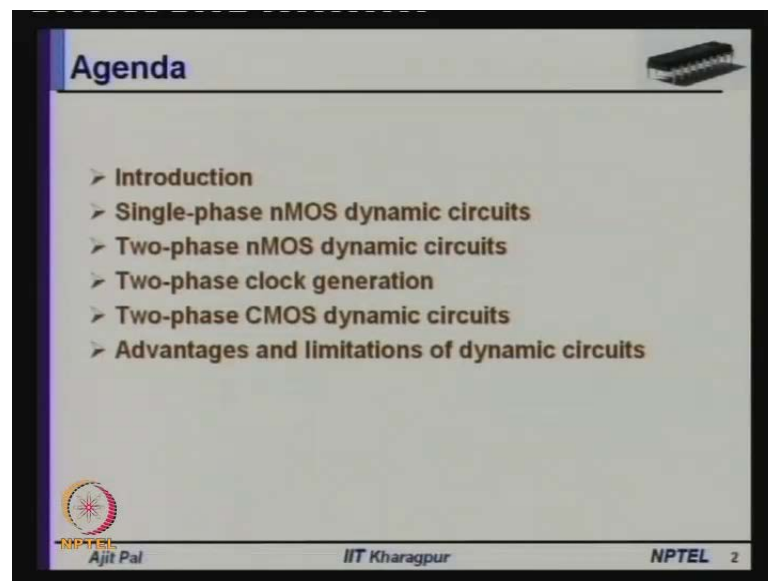


Low Power VLSI Circuits and Systems
Prof. Ajit Pal
Department of Computer Science and Engineering
Indian Institute of Technology, Kharagpur

Lecture No. #12
MOS Dynamic Circuits - I

(Refer Slide Time: 00:37)



Hello and welcome to today's lecture, on MOS dynamic circuits. It is the first lecture on this topic, and in two lectures, I shall consider different aspects of dynamic circuits that are the MOS dynamic circuits. And here is the agenda of today's lecture, after a brief introduction about what we have discussed in my earlier lectures. I shall discuss about single-phase nMOS dynamic circuits although these are not in wide use, but for the sake of completeness, we have to discuss it. Then we shall see discuss about two-phase **two-phase MOS** nMOS dynamic circuits, and also we shall discuss about two-phase clock generation technique followed by two-phase CMOS dynamic circuits. Then finally, I shall conclude our lecture by discussing the advantages and limitation of dynamic circuits.

(Refer Slide Time: 01:22)

Introduction

- Pseudo-nMOS static circuits have two disadvantages:
 - They draw static current as long as power remains ON
 - Because of 'ratioed' logic low-level output is not strong
- No static power dissipation in a CMOS circuit
- But logic function is implemented twice
- Because of the extra area and extra number of transistors, the load capacitance on gates of static CMOS is considerably higher
- Speeds of operation of the static CMOS and pseudo nMOS circuits are comparable
 - The static CMOS has twice the available current drive
 - Static CMOS have twice the capacitance of nMOS
- The trade off in choosing one or the other is between the lower power of the static CMOS and the lower area of pseudo-nMOS

NPTEL 3
Ajit Pal IIT Kharagpur

Coming to the introduction, we have seen that pseudo-nMOS static circuits have two disadvantages. So, they draw static current as long as power remains on and, because of ratioed logic, low-level output is not strong. On the other hand, there is no static power dissipation in CMOS circuits, but logic function is implemented twice.

(Refer Slide Time: 01:54)

$y = x_1 + x_2 x_3$
 $\bar{y} = x_1' \cdot (x_2' x_3')$
Static CMOS

Higher Speed
pseudo-nMOS

Low Power

- Large area
- long delay
- No static power

- smaller area
- smaller delay
- static power

©CET IIT KGP
NPTEL

Let me consider a very simple function say you have to realize y is equal to x_1 plus x_2 x_3 . So, using static CMOS, what will you do? You will realize this function you have to take compliment of this; that means, this will be the compliment of this is x_1 bar dot x_2

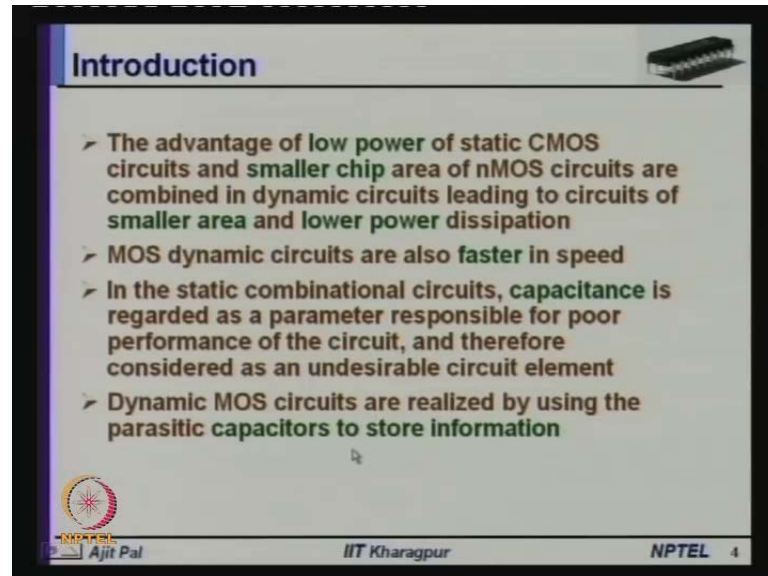
bar x 3 bar. So, this is your y bar. So, the network will correspond to this **this** x bar x 1 bar dot x 2 bar plus x 3 bar. So, the circuit will be like this. So, it will have x 1 x 1 dash and then x 2 dash x 3 dash and these are connected to ground, and the pMOS network will be dual of that; that means, here you will have these are parallel. So, they will be in series. So, x 1 dash and x 2 dash x 3 dash. And you will take the output from here, but if you realize the is the static CMOS and if you realize by using pseudo-nMOS then you do not require. So, many pMOS transistors you require only one pMOS transistor and then the n MOS network part is identical x 1 dash and you will have x 2 dash x 3 dash.

So, we if let us compare the advantages and disadvantages which we have discussed in detail in the last two lectures. So, static CMOS circuits as we can see same functionality is implemented twice in the pMOS network and the nMOS network. So, it requires large area and here you can say smaller area and, because of large area and next stage we will drive both to a p MOS transistor and n MOS transistor, because of that the capacitance is large. So, delay is long longer delay **long delay** primary **primarily**, because of larger area and you have to drive two transistors simultaneously and also; however, the main advantage of this is the power dissipation is there is no static power dissipation. So, no static power dissipation. On the other hand is in case of pseudo small nMOS circuit it has occupies smaller area smaller small delay smaller delay, but there is static power dissipation static power dissipation is there. And it has been found that the pseudo-nMOS circuits can be 5 times faster than that of static CMOS circuits. So, as I mention in my last lecture, we have to combine the advantages of both pseudo-nMOS and static CMOS and we have seen, because of extra area and extra number of transistors the load capacitance of on gates of static CMOS circuits is considerably higher.

So, speeds of operation of static CMOS and pseudo-nMOS circuits are not fairly comparable as I mention that pseudo-n MOS circuits are faster, because the of course, the static CMOS has twice the available current drive, but static CMOS has got twice the capacitance of nMOS. So, although current drive is larger and, but because of larger capacitance delay is longer. So, whenever you have choice between pseudo-nMOS and static CMOS on what basis you will select one from the other if low power is of importance than you will go for your static CMOS. On the other hand higher speed is of requirement then you will go for pseudo-nMOS. Now what we are interested in we

would like to combine the advantages of both of them, and that is why as I mentioned in my last lecture.

(Refer Slide Time: 07:31)



The slide is titled "Introduction" and features a small image of a microchip in the top right corner. It contains a bulleted list of four points:

- The advantage of low power of static CMOS circuits and smaller chip area of nMOS circuits are combined in dynamic circuits leading to circuits of smaller area and lower power dissipation
- MOS dynamic circuits are also faster in speed
- In the static combinational circuits, capacitance is regarded as a parameter responsible for poor performance of the circuit, and therefore considered as an undesirable circuit element
- Dynamic MOS circuits are realized by using the parasitic capacitors to store information

At the bottom of the slide, there are logos for NPTEL, Ajit Pal, IIT Kharagpur, and NPTEL 4.

We shall be going for dynamic CMOS; that means, the advantage of low power of static CMOS circuits and smaller chip area of nMOS circuits or pseudo-nMOS circuits they are same are combined in dynamic circuits leading to circuits of smaller area lower and lower power dissipation; that means, you are achieving both. And also as I mentioned MOS dynamic circuits are also faster in speed. And in the static combinational circuits the capacitance is regarded as a parameter responsible for poor performance of the circuit and therefore, considered as an undesirable circuit element. We have seen that while discussing static CMOS circuit that delay is large, because of larger capacitance. So, the capacitance larger capacitances or presence of capacitances is to be a menace, because of capacitance there is delay and delay is longer if the capacitance is larger.

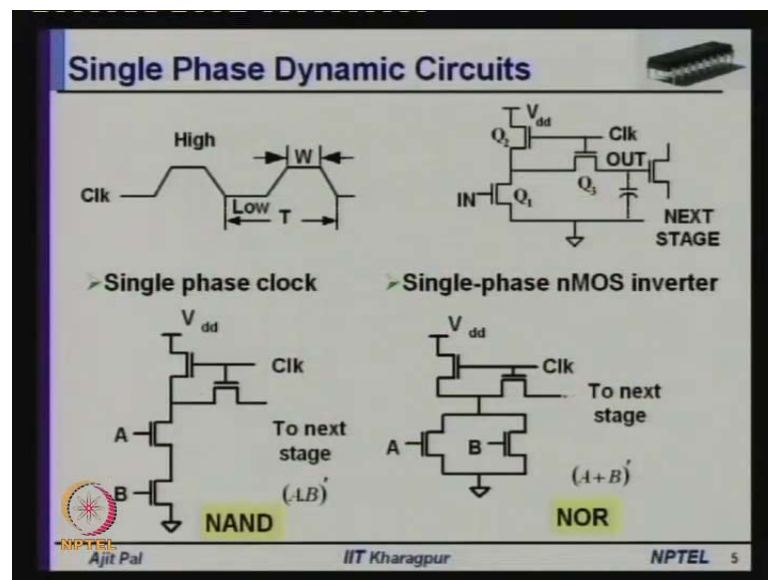
Now, the question arises can the capacitance I am talking about the parasitic capacitances that is present in the circuit, can be used fruitfully can be used can it be used for good cause. So, far it is associated with **with** delay of a circuit, but is there any way by which the capacitances can be utilized to achieve functionality of the circuit which is superior in performance. In fact, that is where the dynamic CMOS comes in **in** dynamic CMOS the capacitor which is present within the MOS circuits we have seen that the that get to substrate or get to channel capacitance. That capacitance is of very

good quality, because of good quality silicon dioxide layer that is created thin oxide layer that is created and that capacitance we shall exploit or utilize how.

We know that a capacitor can be used to store charge. So, since a capacitor can be used to store charge can we develop circuit for the capacitor intrinsic capacitor should be used to store charge and that will be used for implementing circuit operation. And in fact, we shall see that dynamic circuits exactly does that dynamic MOS circuits are realized by using parasitic capacitors to store information. This is also done in a in a memory elements as you know dynamic ram that is used in almost all systems, they are also these the capacitors are utilized to store information, but here we are talking about realizing combinational circuit, by storing information in those parasitic capacitors.

Question naturally arises are they free from any disadvantages; obviously, in this world nothing is one sided we shall as we shall see, it will be dynamic CMOS circuits have many advantages there will be many limitations as well. So, our objective will be to design circuits which will overcome the limitations and utilize the good features.

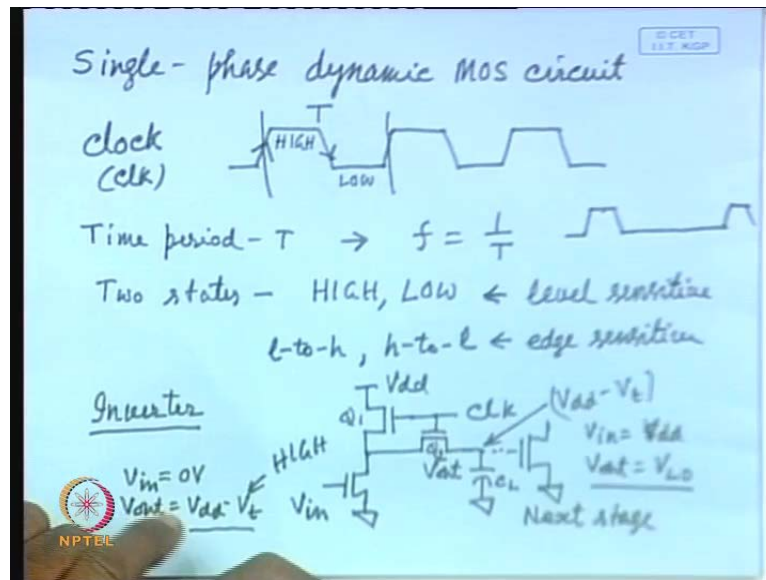
(Refer Slide Time: 11:17)



So, let us proceed to discuss about dynamic circuits to start with we shall discuss about single-phase dynamic circuits although single-phase dynamic circuits are not **not** very common, but for the sake of completeness and for pedagogical purposes. I shall start our discussion we shall start our discussions about single-phase dynamic circuits. One very important point to be noticed at the outset that a dynamic circuit will require some clock.

So, far we have seen that either nMOS or pseudo-nMOS or static CMOS circuits do not require any clock for their operation. So, clock was not present particularly when we are realizing combinational circuit, but as we shall see dynamic circuits will always require some clock.

(Refer Slide Time: 12:20)



So, if in case of your single-phase dynamic MOS circuit you will require some clock. What do you really mean, by clock or how do you characterize a clock. You will be encountering a clock in any digital circuits how do you characterize it you will see that clock is essentially, a train of pulses like this one important feature is the or parameter is the time period t . So, time period is one parameter time period T or it there is another parameter associated with time period that is your frequency **frequency** is equal to 1 by T . So, a clock is characterized by **by** its clock frequency. Now, in addition to that within each cycle. So, this time period is consider a single cycle and this is repeated uh repeated continuously. So, if you look at one particular time period you see that there are two states associated with it one is your high, and another is low so; that means, there are two states what are the two states high and low.

So, these are the two important states which are used to activate circuits. And whenever it is associated with these voltage levels high voltage level and **and** low voltage level we call it level sensitive; that means, the circuit is level sensitive whenever it is a change occurs whenever the circuit is high level or low level depending on that the operation

changes. Another characteristic parameter is also there you know there is you can see each period has got two transitions low to high and high to low. And these are called edge sensitive. They are circuits which are sensitive to edge; that means, here low to high and high to low. So, there are two edges in each period. So, the events can occur or can be initiated either by changing level or by changing edges. So, for as the MOS dynamic circuits are concern as we shall see these are level sensitive; that means, based on level the operation of the circuit changes. Let us draw a very simple single-phase dynamic MOS inverter. How do you realize an inverter, actually you realize you require two transistors connected in this phase, and here you apply a clock say this clock in simple form we usually write is c_1 clock **clock** is applied and here we apply V_{dd} then we have the traditional pull down transistor present here, this is your pull down transistor and we apply an input here, and we take the output not from here, but from this point.

So, here is the output point. So, V_{out} and of course, it will have some associated capacitance as you know, because it is feeding to a next stage and which may be a MOS transistor. So, it is going to the next stage. How it works based on the single-phase clock you have applied a clock here, and you have applied input here, and you are taking the output from here. How it works when this clock is high these transistors q_1 and q_2 both are on. So, when the clock is high both the transistors run, and as a consequence what will happen what get at the output.

Whenever clock is high and input let us assume there are two conditions your V_{in} is equal to 0 volt. Whenever V_{in} is equal to 0 this transistor is off, as a consequence what will happen this capacitor this load capacitor c_1 will charge to V_{dd} through these two transistors and you have applied a clock here. So, these two transistors will remain on. Of course here you will get a voltage which is equal to $V_{dd} - V_t$ not V_{dd} , because you know the transistor will go off as the voltage goes above $V_{dd} - V_t$ V_t is the threshold voltage of the n MOS transistor. So, you are getting a high level voltage which is $V_{dd} - V_t$. Now what about the case now if you whenever the clock is going down; that means, whenever it is in the low level then what happens, then what happens the voltage which is the capacitor which is charged to $V_{dd} - V_t$ that remains there.

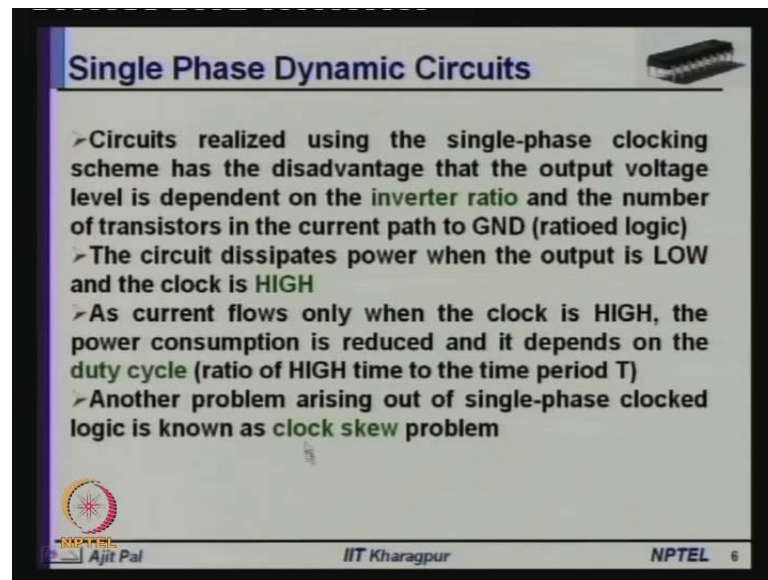
That remains that is available here which we will feed to the next stage; that means, next stage we utilize this logic level; that means, it is assumed that output is now $V_{dd} - V_t$; that means, V_{out} is equal to $V_{dd} - V_t$ which is consider to be high because

input is low. Now, let us consider the situation when V_{in} is equal to say 5 volt or V_{DD} then what will happen whenever it is V_{DD} . Then you can see these transistors are on this transistor is also non on what will be the voltage here, voltage will be dependent on the ratio of the w by l of this transistor and w by l of this transistor. So, the behavior is identical to that of you know static nMOS circuits. So, we get a V_{out} which is equal to V_{low} of course, this is not zero which will be dependent on the ratio of the l by w ratio of these transistor and that is why we can say that this is a **this is a** this is ratioed logic.

Now, what is the gain that we have achieved in this case, gain is that what you can do you can make this period; that means, high level very small. I mean, this period can be small this **this** I mean high level small and low level longer, by that what will what will you achieve you will achieve that power dissipation will occur; that means, this power dissipation can occur only when this clock is high. Earlier respective of the presence of clock as long as output was low, there was power dissipation in static CMOS a static nMOS circuits, but in this particular case only when the output is high. I mean, clock is high and the output is low then there is static power dissipation. So, the static power dissipation is reduced to a great extent, but there is static power dissipation and it is ratioed logic, but the static power dissipation is much lower compared to your static nMOS circuits or pseudo-nMOS circuits; however, you do not get good quality high level and good quality low level both the levels are you know are weak not strong high or strong low.

So, these circuits are not very popular, because of these limitations and although for this say sake of completeness we are discussing it. And In fact, not only inverter you can realized NAND gate as you can see only requirement is that you will require additional transistors in the pMOS nMOS network pull down network. So, to input NAND gate we will require two transistors to neither input nor gate we will require two transistors in this way the number of transistors that is required is equal to n plus 2. So, n number of transistors for the n inputs, and two transistors are required these two transistors q_1 and q_2 . So, these two additional transistors are required apart from n transistors where primary inputs are applied. So, you see the number of transistors is reduced. So, these circuits will be faster than static CMOS; however, we have discussed various limitations of this.

(Refer Slide Time: 22:20)



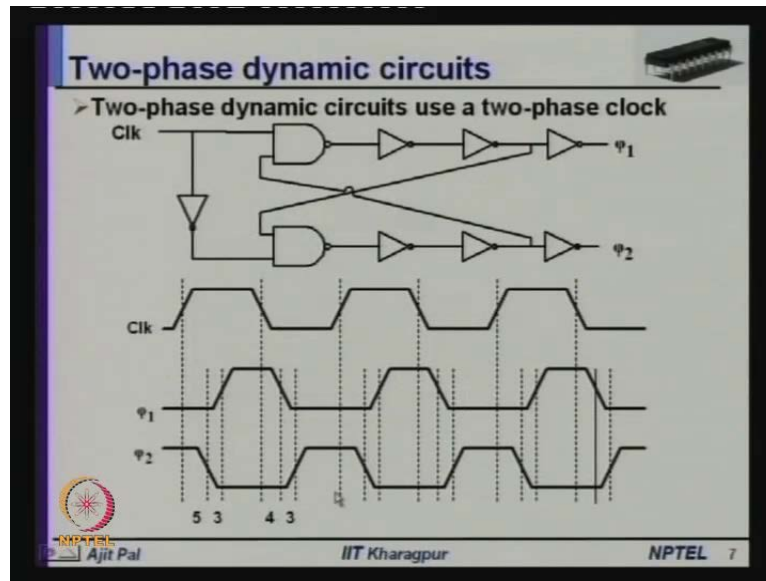
Single Phase Dynamic Circuits

- Circuits realized using the single-phase clocking scheme has the disadvantage that the output voltage level is dependent on the inverter ratio and the number of transistors in the current path to GND (ratioed logic)
- The circuit dissipates power when the output is LOW and the clock is HIGH
- As current flows only when the clock is HIGH, the power consumption is reduced and it depends on the duty cycle (ratio of HIGH time to the time period T)
- Another problem arising out of single-phase clocked logic is known as clock skew problem

NPTEL Ajit Pal IIT Kharagpur NPTEL 6

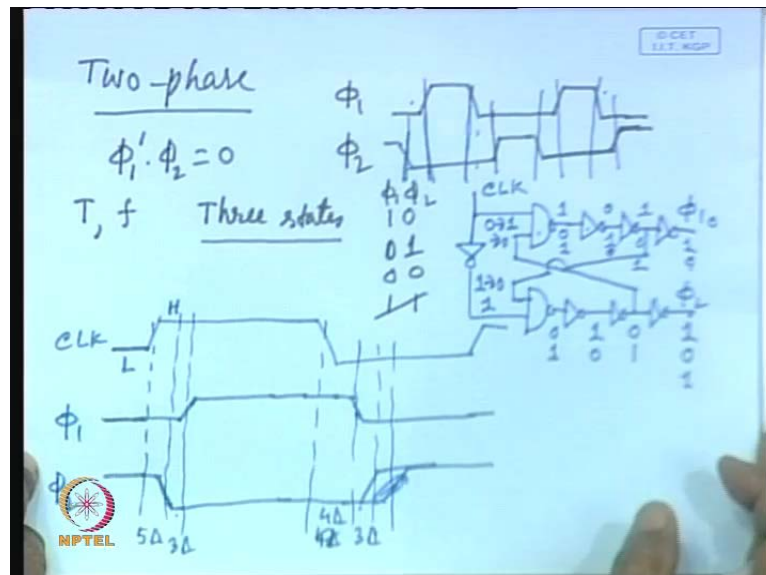
As I mentioned circuits realized using single-phase clock scheme, clocking scheme has the disadvantage that the output voltage level is dependent on the inverter ratio. And the number of transistors in the current part to ground moreover. The circuit dissipates power when the output is low and the clock is high as I mention and as current flows only when the clock is high the power consumption is reduced and it depends on the duty cycle ratio of the high high time to the time period as I mentioned here. So, this is the time period T and this is let us assume this is the this is T 1. So, power dissipation will be dependent on the ratio of T 1 by T and if T 1 is small compared to T 1 by T then power dissipation will be smaller. Another problem arising out of single-phase clocked logic is known as clock skew problem for the timing we are not discussing clock skew problem later on we shall discuss about it in more detail, and let us now switch to two-phase dynamic circuits.

(Refer Slide Time: 23:26)



Now, before we discuss about two-phase dynamic circuits two-phase. What do you really mean by two-phase, before we come to the dynamic circuits let us discuss about what do you really mean by two-phase. In two-phase you will find that there are two clocks not one.

(Refer Slide Time: 23:57)



So; that means, you will be having a clock phi one another clock phi two. So, and they will have some this kind of relationship phi 1 this is phi 1 and phi 2 will be like this they are called non overlapping. By non overlapping we mean, they are never simultaneously

on; that means, $\phi_1 \bar{\phi}_2$ is always 0 as you can see; that means, when ϕ_1 is 1 ϕ_2 is 0 and when ϕ_2 is 1 ϕ_1 is 0. So, what are the different states it can have of course, it will have the time period and frequency like single-phase, but in addition to that what are the other features of a two-phase dynamic two-phase clock number one it has got three states.

Normally whenever you have got two clocks you are supposed to get four states 0 0 1 1 1 0 and 0 1, but here you can see you cannot really have the state when both of them are one; that means, here you will have 1 and 0; that means, ϕ_1 is 1 ϕ_2 is 0. You can have ϕ_2 1 **sorry** ϕ_2 0 ϕ_1 ϕ_1 0 ϕ_2 1, you can have both of them 0 as well for the during this the period both of them 0, but in this case you will never get 1 1; that means, this is not allowed in dynamic in two-phase clock, and that is the reason why it is called two-phase clock.

So, two-phase clock is associated with three states, it is characterize by three states and a and this can be used to realize two-phase dynamic circuits. Question naturally arises how do you realize two-phase clock, because how do you ensure that both of them will never be 1. So, you will require some circuit special type of circuit which can be used to realize a dynamic to realize two-phase clock. Let me draw a very simple diagram which can be used to realize two-phase clock. You will require two NAND gates and several **several** inverters and this is connected to this point and this is connected to this point.

So, here if you apply clock here you will get ϕ_1 and here you will get ϕ_2 let me briefly explain the operation of this circuit. Let us assume this is the clock this is the clock and with respect to with the help of this clock we have generated ϕ_1 and ϕ_2 which are non overlapping in nature. And how they are becoming non overlapping and what will be the gap between this time and this time; that means, when it is going low it is going high or whenever it is going high and this one is going low, these durations these durations are important. So, they should be separated by some gap called band gap. And let us see how it really happens lets such initially let's say here we have assumed that the clock is 0. So, whenever this is 0 what will be the output here, for a NAND gate as you know respective of the number of inputs if any one of the input is 0 output will be 1.

So, since this is 0 this will be 1 this will be 0 this will be 1 and this will be zero; that means, we are getting that ϕ_1 is also 0 when clock is 0 ϕ_1 is also 0. What about ϕ_2 here this since this is 0 this is 1, and here also it is 1. So, 1 makes it 0 this is one this is 0 and this is 1. So, as expected the ϕ_2 is high. So, here it is low and here it is high. Now, at this point it has switched from low to high. So, as it switches from low to high that is 1. What happens whenever it switches to 0 to 1 this will switch to 1 to 0 after 1 gate delay, and as you know for a non gate a NAND gate whenever any one of the input is 0 output will immediately change. So, this will change to 0 to 1 this will change to 1 to 0, this will change to 0 to 1, this will change to 1 to 0 after how much time say how many gate delays 1, 2, 3, 4, 5 after 5 gate delays ϕ_2 is become ϕ_2 is going ϕ_2 is becoming low.

So, let us assume this is the 5 gate delay after 5 gate delay this will go low. Then as you can see here, this is now 1 and this is also 1 these two will make it 0 this will make it one this will make it 0 and this will make it 1. So, this will switch to 1, but how after how much time after this has become say this has become 1 and this is already 1. So, when both of them becomes one after that one two three four; that means, here it will be 1, 2, 3, 4, 5, 6, 7, 8 after 8 gate delays this will switch from 1 to 0 earlier it was one now it will become it has become 0. So, it will become 8 gate delays. So, this is 5 delta and here will be another 3 delta when it will go from low to high.

And this will continue until another change occurs here. So, whenever again it switches from 1 to 0 I mean, 1 to 0 it is switching now to 0. And as it switches to 0 this will now change from 0 to 1 since this is 0 it will become 1 again this will become 0 this will become 1 this will become 0, but after how much time. So, we can see as it is changing from this input is changing from 1 to 0 here 1, 2, 3, 4 after 4 gate delays it will become 0; that means, ϕ_1 will become 0 from this edge after 4 gate delays. And as it has happen this becomes 1 this is also 1, again after three gate delays up from that it will become switch it will switch to 1; that means, this will switch to 1 after 3 gate delays from this 3 gate delays and this will continue.

So, we can see here we have got 5 gate delay here 3 gate delay here 4 gate delay here and this to this it is **sorry** not this 1, this to this 4 gate delay and from this edge to actually it should be here 3 delta. So, we find that in this particular case here, there is a gap of 3 gate delay here also there is gap of 3 gate delay here. Similarly, for the other case also

there will be 3 gate delay; that means, this part this one the gap between these two edges will be 3 delta gap between these two edges will be 3 delta gap between these two edges will be three delta gap between these two edges will be 3 delta.

So, this is how you can realize a two-phase clock with the help of few inverters two NAND gates from a single-phase clock. You may say **say** you may ask that suppose we are not satisfied with a 3 delta band gap between the two-phase clocks. Then what you can do you can insert more number of inverters here, say instead of 3 you can have 5 here then this will become this gap will be 5 delta 5 delta 5 delta and so on. So, depending on your requirement you can increase the gap between the two-phase clocks, but that non overlapping property will be always maintained whenever you will generate two-phase clock by using this technique. So, much about two-phase clock. So, here we have shown the same thing and how continuously you will get two-phase clock phi 1 and phi 2 maintaining 3 gate delays at both edges here also 3 get delay three get delay and so on.

(Refer Slide Time: 34:27)

The slide, titled "Two-phase dynamic circuits", features a circuit diagram on the left and explanatory text on the right. The circuit diagram shows a PMOS transistor Q_1 with gate ϕ_2 and source V_{dd} , and an NMOS transistor Q_2 with gate V_{in} and source ground. The gates of Q_1 and Q_2 are connected to the output node V_0 . A second NMOS transistor Q_3 with gate ϕ_1 and source ground is also connected to V_0 . A capacitor C is connected between V_0 and ground. The text on the right explains the operation: the output is precharged to HIGH during ϕ_2 clock and evaluated during ϕ_1 clock.

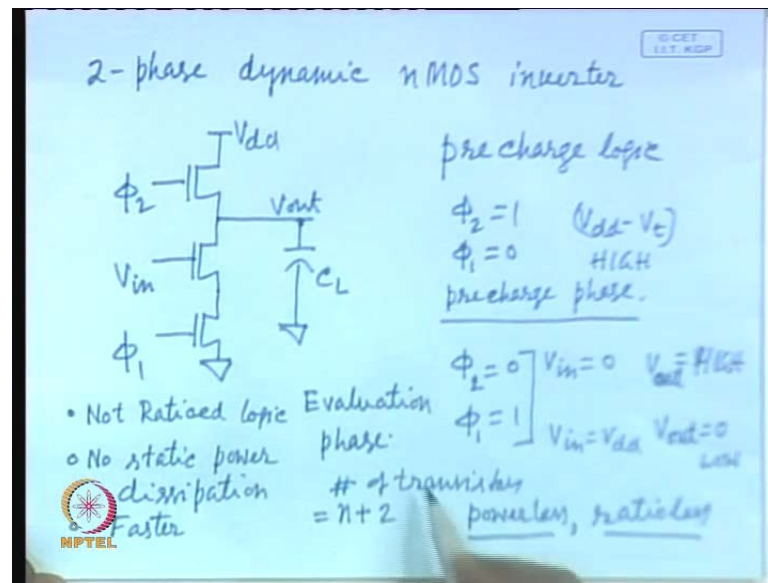
Two-phase dynamic circuits

- > The operation of the circuit can be explained using precharge logic
- > The output is precharged to HIGH level during ϕ_2 clock
- > The output is evaluated during ϕ_1 clock

Ajit Pal IIT Kharagpur NPTEL 8

Now, let us see how we can use this two-phase clock to realize a two-phase dynamic circuit let us consider a two-phase dynamic nMOS inverter.

(Refer Slide Time: 34:38)



So, this will require 3 transistors; that means, here you will apply phi 2 here, you will apply phi 1 this is connected to ground, this is connected to Vdd and V into input is applied here, and you will be taking output from here V out. And as usual to explain the operation of the circuit we shall assume that there is a load capacitance associated with it. Now, let us try to explain the operation of the circuit. The operation of the circuit can be explained with the help of what is known as precharged logic precharged logic. So, when phi 2 is 1 the output and; obviously, that time phi 1 is phi 1 phi 1 is 0, when phi 2 is 1 phi 1 is 0 that we have that we have ensured, both of them can never be simultaneously 1.

So, when this is the case what happens this out this transistor is on. So, this will charge to the output will charge to Vdd minus V t high level output will charge to high level. So, this is called precharged phase. So, during the precharged phase when phi is phi 2 is 1; that means, when phi 2 is 1 the output is charging to high level this is high. Now whenever it switches to phi 2 to 0 and phi 1 is equal to 1 in this condition this transistor is off, and this transistor is on. When this is **this is**, so what will happen to this capacitor this if V in depending on V that now you can have two conditions this is this is known as evaluation phase evaluation phase.

In this evaluation phase there are two possibilities one possibility is that V in is equal to 0, and another possibility is V in is equal to Vdd. Let us consider when V in is equal to 0

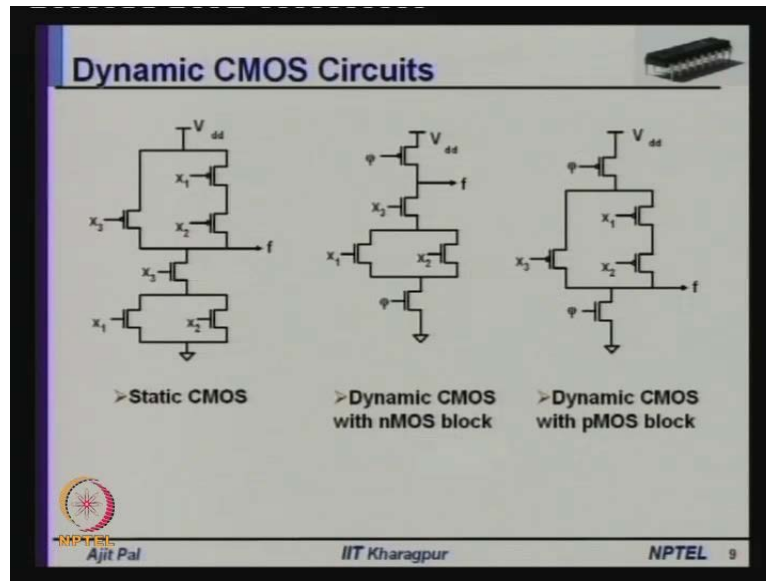
when V_{in} is equal to 0 this transistor is off and although ϕ_2 is 1 this transistor is on there is no path to discharge this capacitor so; that means, V_{out} is equal to V_{DD} I mean is high V_{out} is equal to high why it is high, because which the capacitor has is already charged to high level during the precharged phase. And the evaluation phase follows the precharged phase and as a consequence the high level is maintained during evaluation phase and which will be used by the next stage. So, after evaluation after the evaluation is done a valued output is available which will be used by the next stage.

Now, let us assume V_{in} is equal to V_{DD} . When V_{in} is equal to V_{DD} both the transistors are on and capacitor will discharge to 0 logic level so; that means, in that case V_{out} will be equal to 0 or low logic level. So, here of course, you will get strong low logic level. So, what is the advantage of this circuit we are able to get two possible outputs and of course, high logic level is not very good, but low logic level is good, because it is not ratioed logic. Number one this two-phase dynamic circuit is not ratioed logic. There is no static power dissipation. So, let us list the advantages and disadvantages.

So, maybe we can discuss about the advantages and disadvantages very quickly before we come to other circuits advantages it is not ratioed logic. So, disadvantages associated with ratioed logic is overcome no static power dissipation. Third is faster much faster than either pseudo-n MOS or static CMOS and number of transistors as we have seen is equal to n plus two number of transistors is equal to n plus 2.

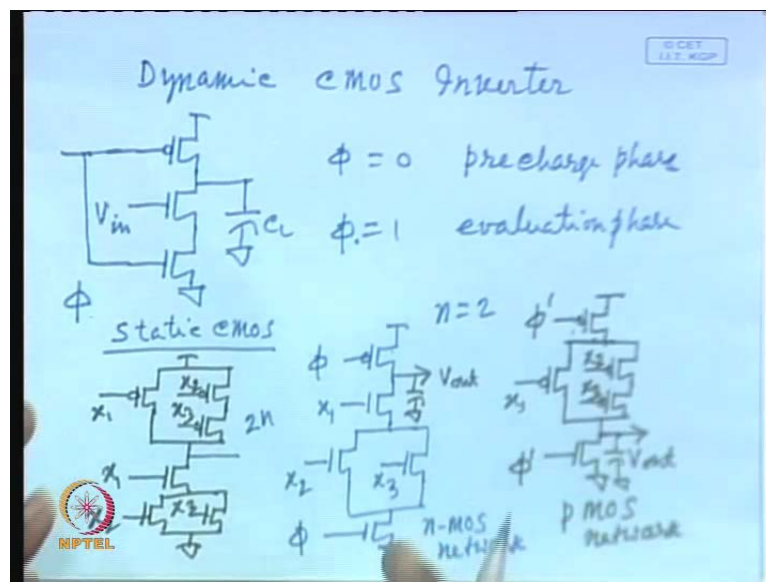
So, these are the advantages of this two-phase dynamics n MOS circuit. So, we find that it has got very good features and that is the reason why it is called powerless ratio less powerless, because there is no static power dissipation and ratio less, because it is not rationed logic and of course, it is faster in operation. So, these two-phase dynamic n MOS inverter is has got very good features and it is widely used; however, you are more interested in u h CMOS circuits.

(Refer Slide Time: 41:05)



So, we can realize dynamic CMOS circuits by extending the idea of static CMOS and here, as you can see how we can do that. Whenever we are using uh statics I mean, by dynamic circuits by using CMOS instead of the nMOS transistor let me redraw it again.

(Refer Slide Time: 41:32)



Instead of using dynamic CMOS inverter let me draw inverter before we can draw the other cycles. So, in case of dynamic inverter what you will require you will require a pMOS transistor as pull up a pull down transistor nMOS transistor for inverter where you will apply input voltage, and a nMOS transistor in the path to 0. So, and what you

can do you can apply a clock you do not really require two-phase clock whenever you are realizing dynamic CMOS circuit the reason for that is you can see the same if we apply the same signal to the pMOS and nMOS transistor, when ϕ is 0 this transistor is on and when ϕ is 1 this transistor is on.

So, that the requirement for that that ϕ_1 and ϕ_2 should not be simultaneously on is satisfied very easily. So, we do not really require two-phase clock in realizing dynamic CMOS circuit. The operation is identical to the inverter that we have discussed two-phase dynamic n MOS inverter here, what happens when when ϕ_2 when ϕ is equal to 0, it is in the precharge phase this output charges to high logic level. And when ϕ is equal to 1 then it is called evaluation phase.

The output is evaluated depending on the input this V_{in} . So, this is how you can realize a dynamic CMOS inverter and all the advantages that I mention in the context of this two-phase dynamic n MOS inverter are applicable to dynamic CMOS inverter. It is not ratioed logic there is no static power dissipation it is faster number of transistor required is equal to $n + 2$ and it is also powerless and ratio less. So, all the advantages are carried to this dynamic CMOS inverter.

You can realize dynamic CMOS inverter I mean, extend this concept to realize more complex gates. Let us consider a first of all static CMOS and we shall see real we shall consider the realization dynamic CMOS circuits corresponding to that. Let us assume that it is little complex circuit. So, you have got say x_1, x_2, x_3 and then you have got x_1, x_2, x_3 connected to down. So, this is your static CMOS circuits we want a dynamic CMOS circuit which is which performs the same function. What we can do you will you may use you can see as I mentioned earlier you are repeating two logic circuits to realize the function we shall see we can use only one of them to realize a dynamic CMOS circuit

Let us see how we can realize this function by using only the n MOS network circuit. So, what will you do you can realize the dynamic CMOS circuits x_1, x_2, x_3 and here you will put one nMOS transistor and here you will put one p MOS transistor and you will apply clock here. So, you can see you do not have really duplicate the logic function here you will require only the nMOS network part which is present here to realize the dynamic CMOS circuit. Of course, you will require two additional transistor that is here you will require $n + 2$ transistors instead of $2n$ as you require in static CMOS.

Now is it the only way to realize dynamic CMOS circuit, actually you can use either the n MOS network or the p MOS network here. The circuit that has been realized is using the n MOS network.

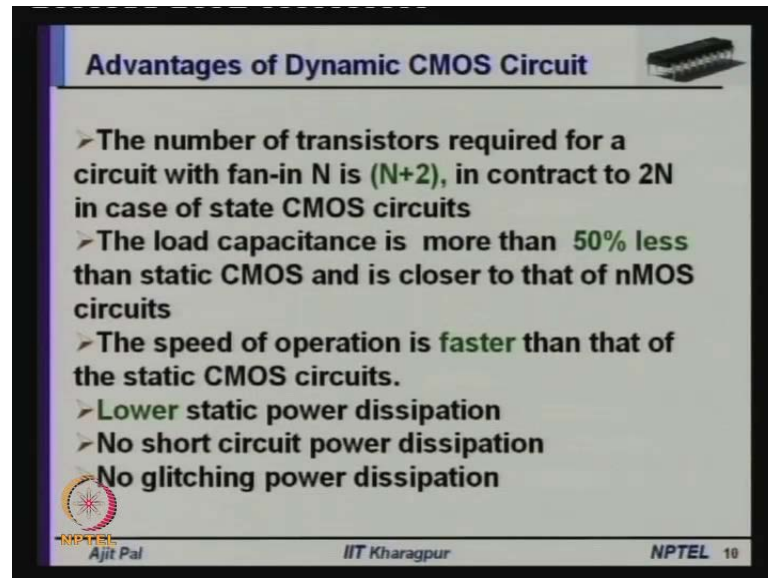
What you can do you can use the same you can realize the same circuit by using the p MOS network. So, in that case the topology will be like this same network x 1, then x 2, x 3, but you will require again two transistors one at the bottom and another the top. So, you will apply ϕ bar you will apply ϕ or you can apply ϕ bar actually. Now, where from you will take the output here you were taking the output from here. So, this was your V_{out} , but whenever used pMOS network in that case you have to take the output from the this point bottom; that means, V_{out} is from here how this circuit operates here actually again it is based on precharge approach, but instead of precharging the output to high level as you do it here you are actually predischarging the output to low level in this particular case; that means, whenever you are using the pMOS network then the output is predischarged during the precharged phase; that means, this transistor is on you have applied ϕ bar. So, this transistor will be on when this is high.

Or ϕ is equal to 0. So, when this is high this transistor will be discharged during precharged phase that is being done. So, this is discharged to 0 and during evaluation what will happen depending on the input combinations input vector; that means, depending on the values of x_1 , x_2 and x_3 , you can uh this output will be charged to high level if the input combination is such the output should be high in that case if there'll be a path through this through this network during the evaluation phase when this transistor is on and the there will be path through this pMOS network. So, this will in the during evaluation phase it will charged to V_{dd} level.

But if the **if the** output is 0 then it will remain in that pre-discharged condition, it will not charged to V_{dd} level. So, you can see we have two possible alternatives whenever we realize circuits using dynamic CMOS approach either you can use the n MOS network or you can use the p MOS network, but you do not have to duplicate; that means, use this as well as that as you do in case of static CMOS and you may have been asking which one will be faster and of course, the network I mean the topology using nMOS network could be faster with the same area, because as you know the pMOS transistors will take uh will take longer time, because of higher resistance and lower mobility of the holes compared to electrons an as a consequence for the same area the this particular topology will be

requiring larger time it will be slower than this one. However both are used later on we shall see both can be combined in realizing a special type of circuit there later on we shall discuss about it for the time being let us restrict to this now very quickly.

(Refer Slide Time: 50:41)



Advantages of Dynamic CMOS Circuit

- The number of transistors required for a circuit with fan-in N is $(N+2)$, in contrast to $2N$ in case of static CMOS circuits
- The load capacitance is more than 50% less than static CMOS and is closer to that of nMOS circuits
- The speed of operation is faster than that of the static CMOS circuits.
- Lower static power dissipation
- No short circuit power dissipation
- No glitching power dissipation

NPTEL Ajit Pal IIT Kharagpur NPTEL 10

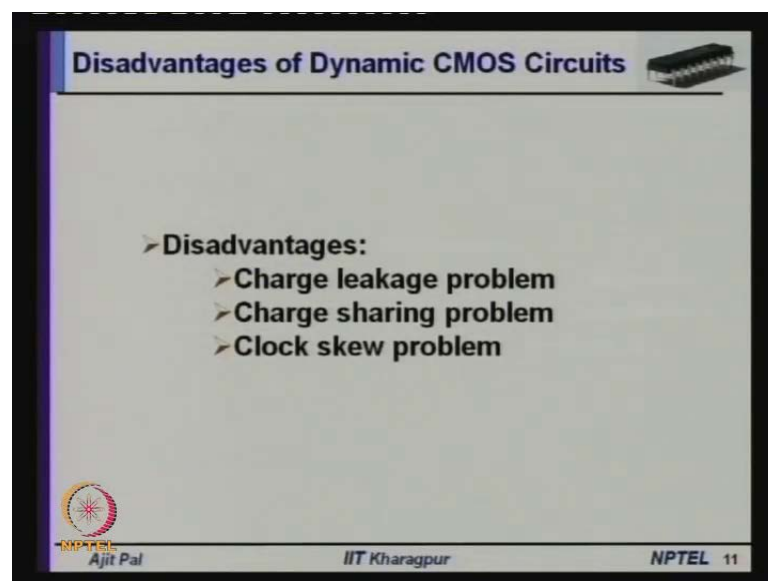
Let us have a look at the disadvantages advantages and disadvantages. As I have already mentioned, the number of transistors required for a circuit with fan-in N is N plus 2 in contrast to $2N$ in case of static CMOS circuits. The load capacitance is more than 50 percent less than static CMOS and is closer to that of nMOS circuits as a consequence it is faster. So, the speed of operation is faster than that of static CMOS circuits about 4 to 5 times faster as we have we have found that; and there is no static power dissipation and another important point is there is no short circuit power dissipation, why there is no short circuit power dissipation, because at no point of time there is path from V_{dd} to ground even when the input changes, because it is controlled by clock and as a consequence it is since it is controlled by clock, there will be no path from V_{dd} to ground at any point of time, and as consequence there is no short circuit power dissipation.

And later on we shall see that it has got no glitching power dissipation why it has got no glitching power dissipation. As you know glitching power dissipation occurs because of you know changes at the output within the circuit, because of the delay of the circuit, but here it is more or less synchronized by clock and only one transition is possible you

know after it has been precharged only transition that can occur is from high to low no other transition is possible, but in case of static CMOS circuits the particular node can go through number of charging and discharging before attempting the final value and as a consequence the glitching power dissipation is not present in dynamic CMOS circuits.

And as a consequence the dynamic CMOS circuits have been found to be very suitable, because of their higher speed of operation and lower area. In fact, one of the very important processor dekalpa chip you may have heard of it that dekalpa processor was one of the fastest processor I mean introduced long back and there they have used about 30 percent of their circuits using dynamic CMOS. Essentially the critical parts of the circuits were implemented by using dynamic CMOS circuit. So, that they can achieve very high speed of operation any way those are the advantages and based on those advantages this is done, but there are several disadvantages.

(Refer Slide Time: 53:17)



Number one is charge leakage problem, number two is charge sharing problem and third is clock skew problem. So, these are the three problems associated with dynamic CMOS circuits. And in my next lecture, I shall discuss about these disadvantages, and also we shall discuss about how they can be overcome. Obviously, if we accept the disadvantages, then we cannot realize a circuit, we have to develop technique by which these limitations and disadvantages can be overcome, and which we shall discuss in my next lecture **thank you**.